

For: METHOD FOR FORMING A METAL OXIDE SEMICONDUCTOR
TYPE FIELD EFFECT TRANSISTOR

AMENDMENT UNDER 37 CFR 1.116

Honorable Commissioner for Patents Washington, D.C. 20231

Sir:

This paper is in response to the Official Action dated December 3, 2002. In that Official Action, Claims 1-18 are rejected under 35 U.S.C. §103(a). Kindly amend the application in accordance with the following particulars: